

**AMENDMENT**

**In The Claims**


Please amend Claim 1 as follows:

1. (Twice Amended) A semiconductor device manufacturing method comprising  
[the steps of ]:

forming a semiconductor film on a substrate;

forming a hydrogen-containing film on said semiconductor film and

irradiating a pulse energy beam to heat said hydrogen-containing film and thereby  
diffuse hydrogen in said hydrogen-containing film into said semiconductor layer;



further comprising irradiating other pulse energy beam to crystallize or re-crystallize  
said semiconductor film after the step of forming said semiconductor film on said substrate  
and before the step of forming said hydrogen-containing film on said semiconductor film,  
energy density of said pulse energy beam used for heating said hydrogen-containing film  
being set lower than energy density of said other pulse energy beam being used to crystallize  
or re-crystallize said semiconductor film.

Please add New Claim 12:

12. The semiconductor device manufacturing method of Claim 1 wherein energy density, number of pulses and pulse width of said pulse energy beam are determined not to melt said semiconductor film.

Please cancel Claim 4, without prejudice or disclaimer.